

14MHz, Rail-to-Rail I/O CMOS Operational Amplifier

1 Features

High Gain Bandwidth:14MHz

 Rail-to-Rail Input and Output ±0.6mV Typical Vos

 Input Voltage Range: -0.1V to +5.6V with Vs = 5.5V

Supply Range: +2.5V to +5.5V

Specified Up To +125°C

Micro Size Packages: SOT23-5

2 Applications

- Sensors
- Photodiode Amplification
- Active Filter
- Test Equipment
- Driving A/D Converters

3 Descriptions

The ZM82X families of products offer low voltage operation and rail-to-rail input and output, as well as excellent speed/power consumption ratio, providing an excellent bandwidth (14MHz) and slew rate of 10V/us. The op-amps are unity gain stable and feature an ultra-low input bias current.

The devices are ideal for sensor interfaces, active filters and portable applications. The ZM82X families of operational amplifiers are specified at the full temperature range of -40°C to +125°C under single or dual power supplies of 2.5V to 5.5V.

Device Information (1)

PART NUMBER	PACKAGE	BODY SIZE(NOM)
ZM821	SOT23-5	2.90mm×1.60mm
ZM822	SOIC-8(SOP8)	4.90mm×3.90mm
ZIVIOZZ	MSOP-8	3.00mm×3.00mm
	SOIC-14	8.65mm×3.90mm
ZM824	(SOP14)	0.00111111/5.90111111
	TSSOP-14	5.00mm×4.40mm

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

REV A.1 1/26

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4 Revision HistoryNote: Page numbers for previous revisions may different from page numbers in the current version.

Version	Change Date	Change Item
C.1	2022/05/25	Initial version completed

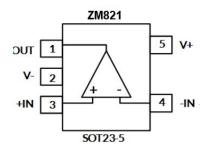


5 Package/Ordering Information (1)

Orderable Device	Package Type	Pin	Channel	Op Temp(°C)	Device Marking ⁽²⁾	MSL ⁽³⁾	Package Qty
ZM821XF	SOT23-5	5	1	-40°C ~125°C	821	MSL3	Tape and Reel,3000
ZM822XK	SOIC-8(SOP8)	8	2	-40°C ~125°C	ZM822	MSL3	Tape and Reel,4000
ZM822XM	MSOP-8	8	2	-40°C ~125°C	ZM822	MSL3	Tape and Reel,4000
ZM824XP	SOIC-14(SOP14)	14	4	-40°C ~125°C	ZM824	MSL3	Tape and Reel,4000
ZM824XQ	TSSOP-14	14	4	-40°C ~125°C	ZM824	MSL3	Tape and Reel,4000

- (1) This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the right-hand navigation.
- (2) There may be additional marking, which relates to the lot trace code information (data code and vendor code), the logo or the environmental category on the device.
- (3) MSL, The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications.

6 Pin Configuration and Functions (Top View)

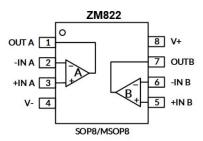


Pin Description

	PIN		
NAME	ZM821	I/O ⁽¹⁾	DESCRIPTION
	SOT23-5		
-IN	4	I	Negative (inverting) input
+IN	3	I	Positive (noninverting) input
OUT	1	0	Output
V-	2	-	Negative (lowest) power supply
V+	5	-	Positive (highest) power supply

 ⁽¹⁾ I = Input, O = Output.
 (2) There is no internal connection. Typically, GND is the recommended connection to a heat spreading plane.

Pin Configuration and Functions (Top View)

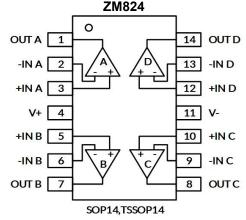


Pin Description

NAME	PIN ZM822 SOIC-8(SOP8)/ MSOP8		I/O ⁽¹⁾	DESCRIPTION
-INA	2		I	Inverting input, channel A
+INA	3		I	Noninverting input, channel A
-INB	6		I	Inverting input, channel B
+INB	5		I	Noninverting input, channel B
OUTA	1		0	Output, channel A
OUTB	7		0	Output, channel B
V-	4		-	Negative (lowest) power supply
V+	8		-	Positive (highest) power supply

⁽¹⁾ I = Input, O = Output.

Pin Configuration and Functions (Top View)



Pin Description

in Description						
PIN	VO (1)	DESCRIPTION				
SOIC-14(SOP14)/TSSOP-14	1,0 ()	DESCRIPTION				
2	I	Inverting input, channel A				
3	I	Noninverting input, channel A				
6	I	Inverting input, channel B				
5	ı	Noninverting input, channel B				
9	I	Inverting input, channel C				
10	I	Noninverting input, channel C				
13	ı	Inverting input, channel D				
12	ı	Noninverting input, channel D				
1	0	Output, channel A				
7	0	Output, channel B				
8	0	Output, channel C				
14	0	Output, channel D				
11	-	Negative (lowest) power supply				
4	-	Positive (highest) power supply				
	PIN SOIC-14(SOP14)/TSSOP-14 2 3 6 5 9 10 13 12 1 7 8 14 11	PIN SOIC-14(SOP14)/TSSOP-14 2				

⁽¹⁾ I = Input, O = Output.

7 Specifications

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT	
	Supply, V _S =(V+) - (V-)		7			
Voltage	Signal input pin ⁽²⁾		(V-)-0.5	(V+) +0.5		
	Signal output pin ⁽³⁾		(V-)-0.5	(V+) +0.5		
	Signal input pin ⁽²⁾		-10	10	mA	
Current	Signal output pin ⁽³⁾		-140	140	mA	
	Output short-circuit (4)			Continuous		
	Package thermal impedance (5)	SOT23-5		230	°C/W	
		SOIC-8(SOP8)		110.88		
θ_{JA}		MSOP-8		165.7		
		SOIC-14(SOP14)		104.5		
		TSSOP-14		89.21		
	Operating range, T _A	-40	125			
Temperature	Junction, T _J ⁽⁶⁾		-40	150	°C	
	Storage, T _{stg}		-65	150	_	

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

7.2 ESD Ratings

The following ESD information is provided for handling of ESD-sensitive devices in an ESD protected area only.

		· ·		VALUE	UNIT
V	V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-00	1 ⁽¹⁾	±5000	\/
V _(ESD)	Electrostatic discharge	Machine Model (MM)		±400	'

⁽¹⁾ JEDEC document JEP155 states that 500 V HBM allows safe manufacturing with a standard ESD control process.



ESD SENSITIVITY CAUTION

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

⁽²⁾ Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.

⁽³⁾ Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±140mA or less.

⁽⁴⁾ Short-circuit to ground, one amplifier per package.

⁽⁵⁾ The package thermal impedance is calculated in accordance with JESD-51.

⁽⁶⁾ The maximum power dissipation is a function of T_{J(MAX)}, R_{8JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)} - T_A) / R_{6JA}. All numbers apply for packages soldered directly onto a PCB.



7.3 Recommended Operating ConditionsOver operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage , V _S = (V+) - (V-)	Single-supply	2.5		5.5	
Supply voltage , V _S = (V+) - (V-)	Dual-supply	±1.25		±2.75	V

7.4 Electrical Characteristics

(At T_A = +25°C, V_S =5V, R_L = 10k Ω connected to $V_S/2$, and V_{OUT} = $V_S/2$, V_{CM} = $V_S/2$, Full $^{(9)}$ = -40°C to +125°C, unless otherwise noted.) $^{(1)}$

	DADAMETED	CONDITIONS	_	Z	ZM821, ZM822, ZM824			
	PARAMETER	CONDITIONS	TJ	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNIT	
POWER	RSUPPLY				'			
Vs	Operating Voltage Range		25°C	2.5		5.5	V	
ΙQ	Quiescent Current/Amplifier		25°C		1.9	2.5	mA	
DCDD	Davier Comply Daineties Datin	V _S =2.5V to 5.5V	25°C	75	88		40	
PSRR	Power-Supply Rejection Ratio	V _{CM} = (V-)+0.5V	Full	65			dB	
INPUT								
Vos	Input Offset Voltage	V _{CM} = V _S /2	25°C	-2.5	±0.6	2.5	mV	
$V_{\text{OS}}T_{\text{C}}$	Input Offset Voltage Average Drift	V _{CM} = V _S /2	Full		±1.6		uV/°C	
lΒ	Input Bias Current (4) (5)		25°C		±1	±10	pА	
los	Input Offset Current (4)		25°C		±1	±10	pА	
V _{СМ}	Common-Mode Voltage Range	V _S = 5.5V	25°C	-0.1		5.6	V	
	Common-Mode Rejection Ratio	V _S = 5.5V, V _{CM} =-0.1V to 4V	25°C	75	88		- dB	
CMRR			Full	67				
		V _S = 5.5V, V _{CM} =-0.1V to 5.6V	25°C	61	75			
			Full	58				
OUTPU	Т							
		$R_L=2K\Omega$,	25°C	91	100		dB	
Aol	Open-Loop Voltage Gain	Vo=0.15V to 4.85V	Full	78				
AOL	Open-Loop voltage Gain	R _L =10KΩ,	25°C	89	98			
		Vo= 0.05V to 4.95V	Full	75				
	Output Swing From Rail	R _L =2KΩ	25°C		20		mV	
	Output Swing From Kaii	R _L =10KΩ	25 C		7		1110	
I _{OUT}	Output Short-Circuit Current (6) (7)		25°C		±110		mA	
FREQU	ENCY RESPONSE							
SR	Slew Rate (8)		25°C		10		V/us	
GBP	Gain-Bandwidth Product		25°C		14		MHz	
PM	Phase Margin		25°C		58		۰	
ts	Setting Time,0.1%				0.2		us	
	Overload Recovery Time	V _{IN} ·Gain≥V _S			0.3		us	
NOISE								
	Input Voltage Noise Density	f = 1KHz	25°C		8.5		nV/√Hz	
e _n	input voitage noise Density	f = 10KHz	25°C		5.5		nV/√Hz	

- (1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.
- (2) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.
- (3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration.
- (4) This parameter is ensured by design and/or characterization and is not tested in production.
- (5) Positive current corresponds to current flowing into the device.
- (6) The maximum power dissipation is a function of $T_{J(MAX)}$, $R_{\theta JA}$, and T_A . The maximum allowable power dissipation at any ambient temperature is PD = $(T_{J(MAX)} T_A) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.



- (7) Short circuit test is a momentary test.(8) Number specified is the slower of positive and negative slew rates.(9) Specified by characterization only.

7.5 Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At $T_A = +25^{\circ}\text{C}$, $V_S = 5\text{V}$, $R_L = 10\text{k}\Omega$ connected to $V_S/2$, $V_{OUT} = V_S/2$, unless otherwise noted.

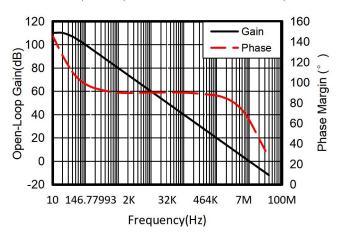


Figure 1. Open-Loop Gain and Phase vs Frequency

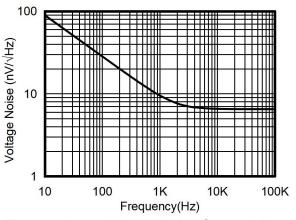


Figure 3. Input Voltage Noise Spectral Density vs Frequency

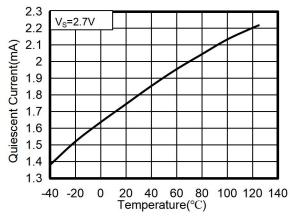


Figure 5. Quiescent Current vs Temperature

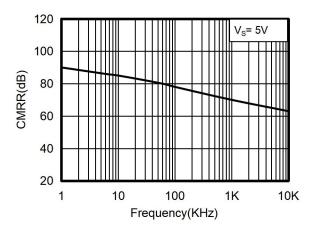


Figure 2. Common-Mode Rejection Ratio vs Frequency

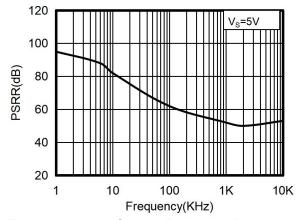


Figure 4. Power-Supply Rejection Ratio vs Frequency

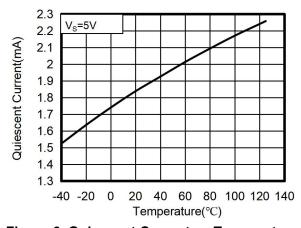


Figure 6. Quiescent Current vs Temperature

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At $T_A = +25^{\circ}C$, $V_S=5V$, $R_L = 10k\Omega$ connected to $V_S/2$, $V_{OUT} = V_S/2$, unless otherwise noted.

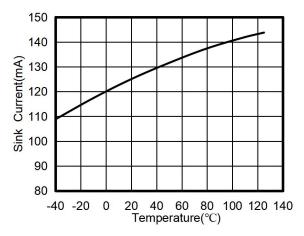


Figure 7. Sink Current vs Temperature

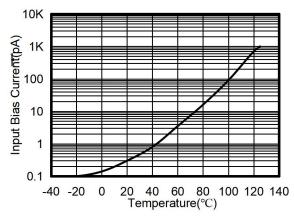


Figure 9. Input Bias Current vs Temperature

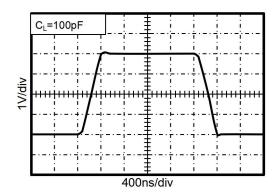


Figure 11. Large-Signal Step Response

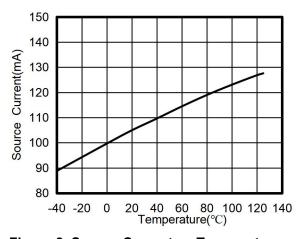


Figure 8. Source Current vs Temperature

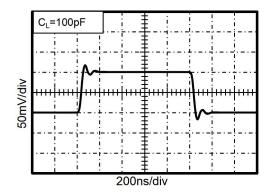


Figure 10. Small-Signal Step Response

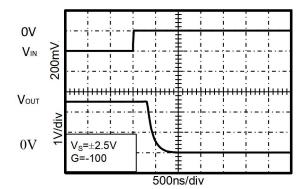


Figure 12. Positive Overvoltage Recovery

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, V_S =5V, R_L = 10k Ω connected to $V_S/2$, V_{OUT} = $V_S/2$, unless otherwise noted.

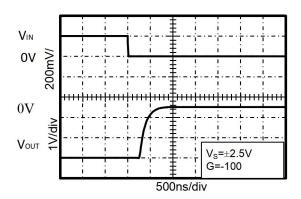


Figure 13. Negative Overvoltage Recovery

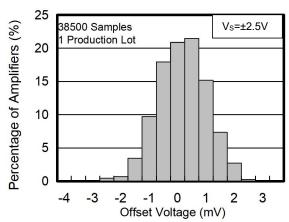


Figure 14. Offset Voltage Production Distribution

8 Detailed Description

8.1 Overview

The ZM821, ZM822, ZM824, are high precision, rail-to-rail operational amplifiers that can be run from a single-supply voltage 2.5V to 5.5V (±1.25V to ±2.75V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications. Good layout practice mandates use of a 0.1uF capacitor place closely across the supply pins.

8.2 Phase Reversal Protection

The ZM82X family has internal phase-reversal protection. Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the ZM82X prevents phase reversal with excessive common-mode voltage. Instead, the appropriate rail limits the output voltage. This performance is shown in figure 15.

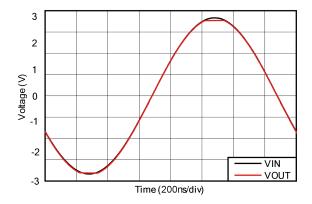


Figure 15. Output Waveform Devoid of Phase Reversal During an Input Overdrive Condition

8.3 EMI Rejection Ratio (EMIRR)

The electromagnetic interference (EMI) rejection ratio, or EMIRR, describes the EMI immunity of operational amplifiers. An adverse effect that is common to many operational amplifiers is a change in the offset voltage as a result of RF signal rectification. An operational amplifier that is more efficient at rejecting this change in offset as a result of EMI has a higher EMIRR and is quantified by a decibel value. Measuring EMIRR can be performed in many ways, but this document provides the EMIRR IN+, which specifically describes the EMIRR performance when the RF signal is applied to the noninverting input pin of the operational amplifier. In general, only the noninverting input is tested for EMIRR for the following three reasons:

- Operational amplifier input pins are known to be the most sensitive to EMI, and typically rectify RF signals better than the supply or output pins.
- The noninverting and inverting operational amplifier inputs have symmetrical physical layouts and exhibit nearly matching EMIRR performance.
- EMIRR is easier to measure on noninverting pins than on other pins because the noninverting input pin can be isolated on a printed-circuit-board (PCB). This isolation allows the RF signal to be applied directly to the noninverting input pin with no complex interactions from other components or connecting PCB traces.

Detailed Description (continued)

The EMIRR IN+ of the ZM82X is plotted versus frequency in Figure 16. If available, any dual and quad operational amplifier device versions have approximately identical EMIRR IN+ performance. The ZM82X unity-gain bandwidth is 14MHz. EMIRR performance below this frequency denotes interfering signals that fall within the operational amplifier bandwidth.

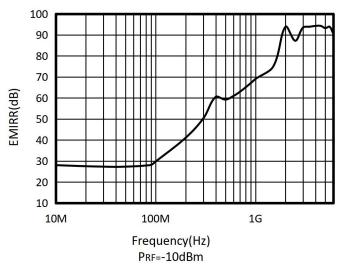


Figure 16. ZM82X EMIRR vs Frequency

8.4 EMIRR IN+ Test Configuration

Figure 17 shows the circuit configuration for testing the EMIRR IN+. An RF source is connected to the operational amplifier noninverting input pin using a transmission line. The operational amplifier is configured in a unity-gain buffer topology with the output connected to a low-pass filter (LPF) and a digital multimeter (DMM). A large impedance mismatch at the operational amplifier input causes a voltage reflection; however, this effect is characterized and accounted for when determining the EMIRR IN+. The resulting dc offset voltage is sampled and measured by the multimeter. The LPF isolates the multimeter from residual RF signals that can interfere with multimeter accuracy.

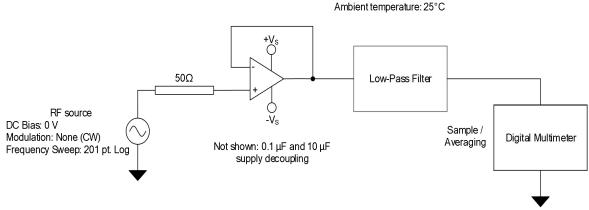


Figure 17. EMIRR IN+ Test Configuration Schematic

9 Application and Implementation

Information in the following applications sections is not part of the Z-Micro component specification, and Z-Micro does not warrant its accuracy or completeness. Z-Micro's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Note

The ZM82X are high precision, rail-to-rail operational amplifiers that can be run from a single-supply voltage 2.5V to 5.5V (±1.25V to ±2.75V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications. Good layout practice mandates use of a 0.1uF capacitor place closely across the supply pins.

Typical Applications 9.2 25-kHz Low-pass Filter

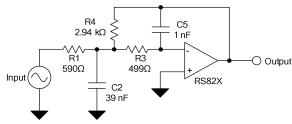


Figure 18. 25-kHz Low-Pass Filter

9.3 Design Requirements

Low-pass filters are commonly employed in signal processing applications to reduce noise and prevent aliasing. The ZM82X devices are ideally suited to construct high-speed, high-precision active filters. Figure 18 shows a second-order, low-pass filter commonly encountered in signal processing applications.

Use the following parameters for this design example:

- Gain = 5 V/V (inverting gain)
- Low-pass cutoff frequency = 25 kHz
- · Second-order Chebyshev filter response with 3-dB gain peaking in the passband

9.4 Detailed Design Procedure

The infinite-gain multiple-feedback circuit for a low-pass network function is shown in Figure 18. Use Equation 1 to calculate the voltage transfer function.

$$\frac{\text{Output}}{\text{Input}}(s) = \frac{-\frac{1}{1}R_{1}R_{3}C_{2}C_{5}}{s^{2} + (s/C_{2})(\frac{1}{1}R_{1} + \frac{1}{1}R_{3} + \frac{1}{1}R_{4}) + \frac{1}{1}R_{3}R_{4}C_{2}C_{5}}$$
(1)

This circuit produces a signal inversion. For this circuit, the gain at dc and the low-pass cutoff frequency are calculated by Equation 2:

Gain =
$$\frac{R_4}{R_1}$$

 $f_C = \frac{1}{2\pi} \sqrt{(1/R_3 R_4 C_2 C_5)}$

(2)

9.5 Application Curve

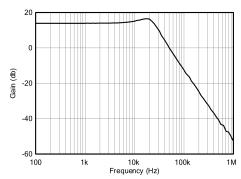


Figure 19. Low-pass filter transfer function

10 Layout

10.1 Layout Guidelines

Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.

10.2 Layout Example

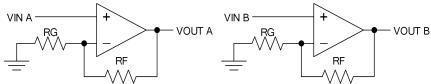


Figure 20. Schematic Representation

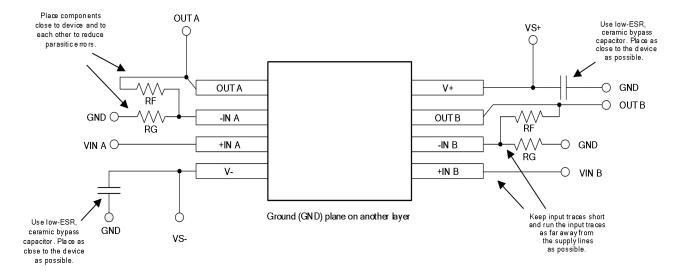
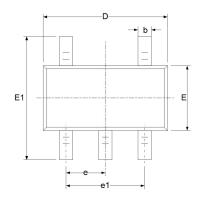
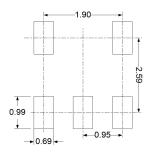


Figure 21. Layout Example

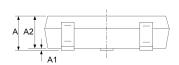
NOTE: Layout Recommendations have been shown for dual op-amp only, follow similar precautions for Single and four.

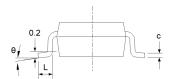
11 Package Outline Dimensions SOT23-5





RECOMMENDED LAND PATTERN (Unit: mm)





Comple of	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
А	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037	(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

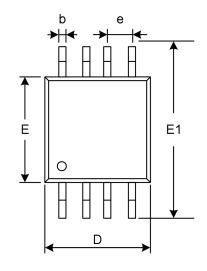
NOTE:

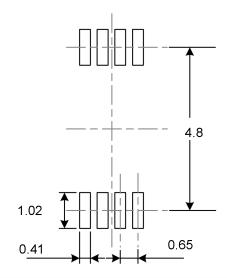
A. This drawing is subject to change without notice.

B. Plastic or metal protrusions of 0.15mm maximum per side are not included.

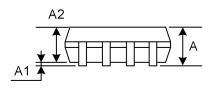
C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

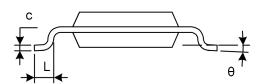
MSOP8





RECOMMENDED LAND PATTERN (Unit: mm)



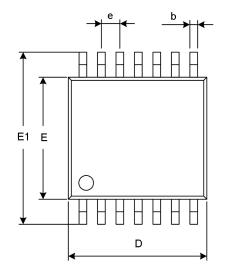


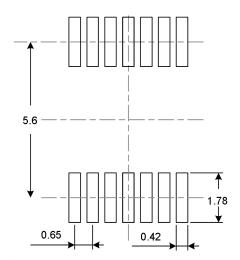
Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А	0.820	1.100	0.032	0.043		
A1	0.020 0.150 0.001		0.001	0.006		
A2	0.750	0.950	0.030	0.037		
b	0.250	0.380	0.010	0.015		
С	0.090	0.230	0.004	0.009		
D	2.900	3.100	0.114	0.122		
е	0.650	(BSC)	0.026(BSC)			
Е	2.900	3.100	0.114	0.122		
E1	4.750	5.050	0.187	0.199		
L	0.400	0.800	0.016	0.031		
θ	0°	6°	0°	6°		

- A. This drawing is subject to change without notice.

 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
- C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

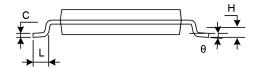
TSSOP-14











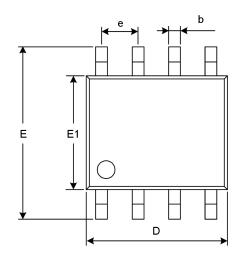
Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А		1.200		0.047		
A1	0.050	0.150	0.002	0.006		
A2	0.800	1.050	0.031	0.041		
b	0.190	0.300	0.007	0.012		
С	0.090	0.200	0.004	0.008		
D	4.860	5.100	0.191	0.201		
E	4.300	4.500	0.169	0.177		
E1	6.250	6.550	0.246	0.258		
е	0.650(BSC)		0.026(BSC)			
L	0.500	0.700	0.020	0.028		
Н	0.25(TYP)		0.01(TYP)			
θ	1°	7°	1°	7°		

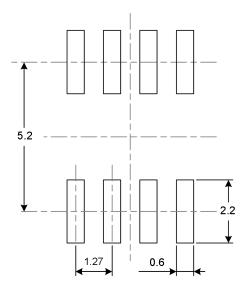
- A. This drawing is subject to change without notice.

 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.

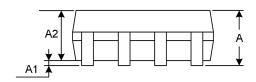
 C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

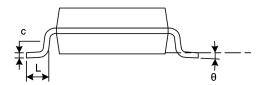
SOIC-8(SOP8)





RECOMMENDED LAND PATTERN (Unit: mm)



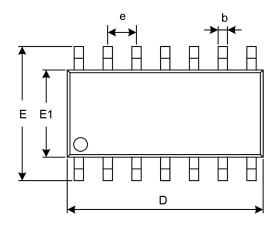


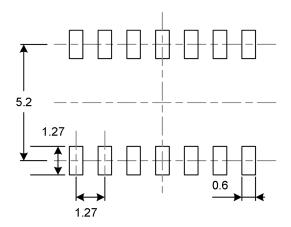
Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
A	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
С	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0.197		
е	1.270	(BSC)	0.050(BSC)			
E	5.800	6.200	0.228	0.244		
E1	3.800	4.000	0.150	0.157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		

- A. This drawing is subject to change without notice.

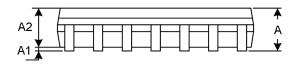
 B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
- C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

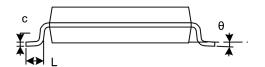
SOIC-14(SOP14)





RECOMMENDED LAND PATTERN (Unit: mm)





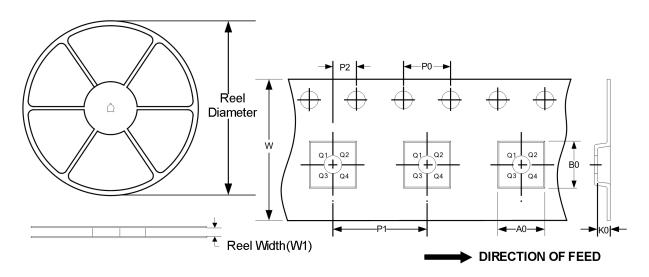
Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
	Min	Max	Min	Max		
А	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.310	0.510	0.012	0.020		
С	0.100	0.250	0.004	0.010		
D	8.450	8.850	0.333	0.348		
е	1.270	(BSC)	0.050(BSC)			
Е	5.800	6.200	0.228	0.244		
E1	3.800	4.000	0.150	0.157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		

NOTE:

A. This drawing is subject to change without notice.
B. Plastic or metal protrusions of 0.15mm maximum per side are not included.
C. BSC: Basic Dimension. Theoretically exact value shown without tolerances.

12 Tape and Reel Information REEL DIMENSIONS

TAPE DIMENSION



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width(mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOT23-5	7"	9.5	3.20	3.20	1.40	4.0	4.0	2.0	8.0	Q3
SOIC-8(SOP8)	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
MSOP-8	13"	12.4	5.20	3.30	1.50	4.0	8.0	2.0	12.0	Q1
SOIC-14(SOP14)	13"	16.4	6.60	9.30	2.10	4.0	8.0	2.0	16.0	Q1
TSSOP-14	13"	12.4	6.95	5.60	1.20	4.0	8.0	2.0	12.0	Q1

NOTE

^{1.} All dimensions are nominal.

^{2.} Plastic or metal protrusions of 0.15mm maximum per side are not included.

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